1	2	("6222225").PN.	USPAT;	2004/07/20 11:08
ļ		( 022223 ).111.	•	2004/07/20 11:00
			US-PGPUB;	
			ЕРО; ЈРО;	
2	5324	257/239,261,298,315-326.ccls.	DERWENT;	
			IBM_TDB	
			USPAT;	2004/07/20 11:08
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
3	4472	438/201,211,216,241,257,258,260-266,591,593.ccls.	USPAT;	2004/07/20 11:10
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
4	9114	257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.	USPĀT;	2004/07/20 11:10
`			US-PGPUB;	
		······································	ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
5	1987	(257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:43
	1,0,	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)	ЕРО; ЈРО;	İ
		Volume field memory	DERWENT;	
			IBM_TDB	
6	186	((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:18
Ü	100	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЛРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric)))	DERWENT;	
		distribution) with (second field Bute field (missianes sines are re-	IBM_TDB	
7	32	(((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:14
′	] 32	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЈРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric))))	DERWENT;	
		and ((first near thick\$4) with (second near thick\$4))	IBM TDB	
8	68	((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:38
Ů	00	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЛРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric)) with	DERWENT;	
		thick\$4)	IBM_TDB	
9	8	((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:43
	l	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЛРО;	
		dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide	DERWENT;	
		dielectric) near thick\$4))	IBM_TDB	
10	349594	257/\$.ccls. 438/\$.ccls.	USPAT;	2004/07/20 11:43
10			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
11	5004	(257/\$.ccls. 438/\$.ccls.) and (non near volatile near memory)	USPAT;	2004/07/20 11:49
		(	US-PGPUB;	
			ЕРО; ЛРО;	
i			DERWENT;	
			IBM_TDB	
12	. 15	((257/\$.ccls. 438/\$.ccls.) and (non near volatile near memory)) and	USPAT;	2004/07/20 11:49
12	. 13	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	US-PGPUB;	
		(second near gate near (insulat\$3 oxide dielectric) near thick\$4))	ЕРО; ЛРО;	
Ì		1 (		1
			DERWENT:	
			DERWENT; IBM_TDB	į

14	60231	non near volatile near memory	USPAT;	2004/07/20 11:49
		·	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
15	16	(non near volatile near memory) and ((first near gate near (insulat\$3	USPAT;	2004/07/20 11:55
		oxide dielectric) near thick\$4) with (second near gate near (insulat\$3	US-PGPUB;	
		oxide dielectric) near thick\$4))	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
16	44	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	USPAT;	2004/07/20 11:52
		(greater bigger larger) with (second near gate near (insulat\$3 oxide	US-PGPUB;	
		dielectric) near thick\$4))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	179	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	USPAT;	2004/07/20 11:55
		(second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	